

ON Semiconductor

Is Now

onsemi™

To learn more about onsemi™, please visit our website at
www.onsemi.com

onsemi and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.

NTD4965N

MOSFET – Power, Single, N-Channel, DPAK/IPAK

30 V, 68 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- Three Package Variations for Design Flexibility
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- CPU Power Delivery
- DC-DC Converters

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit		
Drain-to-Source Voltage	V_{DSS}	30	V		
Gate-to-Source Voltage	V_{GS}	± 20	V		
Continuous Drain Current $R_{\theta JA}$ (Note 1)	I_D	$T_A = 25^\circ\text{C}$	17.8	A	
		$T_A = 100^\circ\text{C}$	12.6		
Power Dissipation $R_{\theta JA}$ (Note 1)	P_D	$T_A = 25^\circ\text{C}$	2.6	W	
Continuous Drain Current $R_{\theta JA}$ (Note 2)	I_D	$T_A = 25^\circ\text{C}$	13.0	A	
		$T_A = 100^\circ\text{C}$	9.2		
Power Dissipation $R_{\theta JA}$ (Note 2)	P_D	$T_A = 25^\circ\text{C}$	1.39	W	
Continuous Drain Current $R_{\theta JC}$ (Note 1)	I_D	$T_C = 25^\circ\text{C}$	68	A	
		$T_C = 100^\circ\text{C}$	48		
Power Dissipation $R_{\theta JC}$ (Note 1)	P_D	$T_C = 25^\circ\text{C}$	38.5	W	
Pulsed Drain Current	$t_p = 10\mu\text{s}$	$T_A = 25^\circ\text{C}$	I_{DM}	248	A
Current Limited by Package		$T_A = 25^\circ\text{C}$	$I_{DmaxPkg}$	76	A
Operating Junction and Storage Temperature	T_J, T_{STG}			-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	I_S			35	A
Drain to Source dV/dt	dV/dt			6.0	V/ns
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 24\text{ V}$, $V_{GS} = 10\text{ V}$, $I_L = 31\text{ A}_{pk}$, $L = 0.1\text{ mH}$, $R_G = 25\ \Omega$)	EAS			47	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L			260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

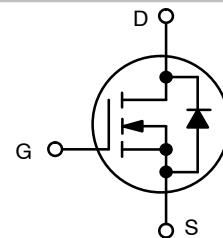
1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.



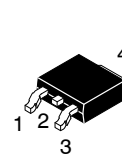
ON Semiconductor®

<http://onsemi.com>

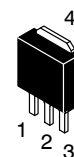
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
30 V	4.7 m Ω @ 10 V	68 A
	10 m Ω @ 4.5 V	



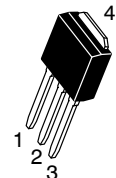
N-CHANNEL MOSFET



CASE 369AA
DPAK
(Bent Lead)
STYLE 2

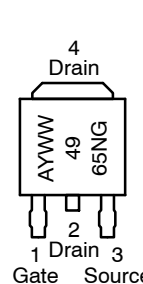


CASE 369AC
3 IPAK
(Straight Lead)

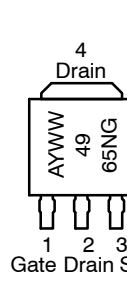


CASE 369D
IPAK
(Straight Lead
DPAK)

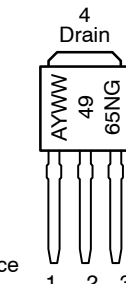
MARKING DIAGRAMS & PIN ASSIGNMENTS



1 Drain 3
Gate Source



1 2 3
Gate Drain Source



1 2 3
Gate Drain Source

- A = Assembly Location
- Y = Year
- WW = Work Week
- 4965N = Device Code
- G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

NTD4965N

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	3.9	°C/W
Junction-to-TAB (Drain)	$R_{\theta JC-TAB}$	4.3	
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	57.6	
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	107.6	

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			21.5		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.5	1.8	2.5	V	
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			4.1		mV/°C	
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 30\text{ A}$		3.4	4.7	m Ω
			$I_D = 15\text{ A}$		3.4		
		$V_{GS} = 4.5\text{ V}$	$I_D = 30\text{ A}$		5.4	10	
			$I_D = 15\text{ A}$		5.3		
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}, I_D = 30\text{ A}$		52		S	

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 15\text{ V}$		1710		pF
Output Capacitance	C_{OSS}			664		
Reverse Transfer Capacitance	C_{RSS}			340		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		17.2		nC
Threshold Gate Charge	$Q_{G(TH)}$			2.7		
Gate-to-Source Charge	Q_{GS}			5.1		
Gate-to-Drain Charge	Q_{GD}			8.5		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		28.2		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$		12.1		ns
Rise Time	t_r			34.2		
Turn-Off Delay Time	$t_{d(OFF)}$			18.9		
Fall Time	t_f			14.2		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

7. Assume terminal length of 110 mils.

NTD4965N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 6)						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$		8.3		ns
Rise Time	t_r			21.5		
Turn-Off Delay Time	$t_{d(OFF)}$			24.4		
Fall Time	t_f			7.8		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 30\text{ A}$	$T_J = 25^\circ\text{C}$		0.86	1.1	V
			$T_J = 125^\circ\text{C}$		0.74		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 30\text{ A}$			28.3		ns
Charge Time	t_a				13.3		
Discharge Time	t_b				15		
Reverse Recovery Charge	Q_{RR}				16		

PACKAGE PARASITIC VALUES

Source Inductance (Note 7)	L_S	$T_A = 25^\circ\text{C}$		2.85		nH
Drain Inductance, DPAK	L_D			0.0164		
Drain Inductance, IPAK (Note 7)	L_D			1.88		
Gate Inductance (Note 7)	L_G			4.9		
Gate Resistance	R_G			1.0	2.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
6. Switching characteristics are independent of operating junction temperatures.
7. Assume terminal length of 110 mils.

ORDERING INFORMATION

Device	Package	Shipping [†]
NTD4965NT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NTD4965N-1G	IPAK (Pb-Free)	75 Units / Rail
NTD4965N-35G	IPAK Trimmed Lead (Pb-Free)	75 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL PERFORMANCE CURVES

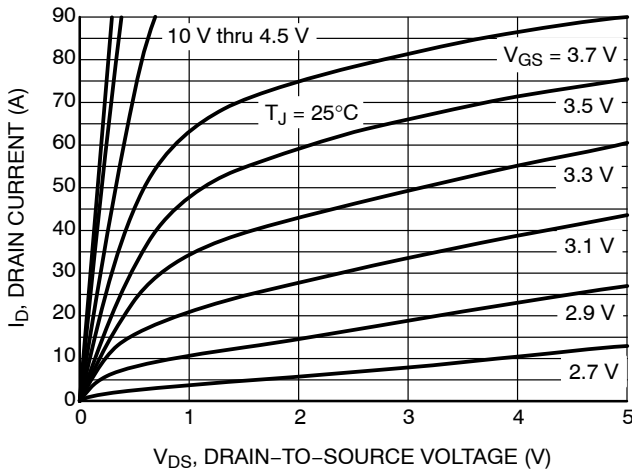


Figure 1. On-Region Characteristics

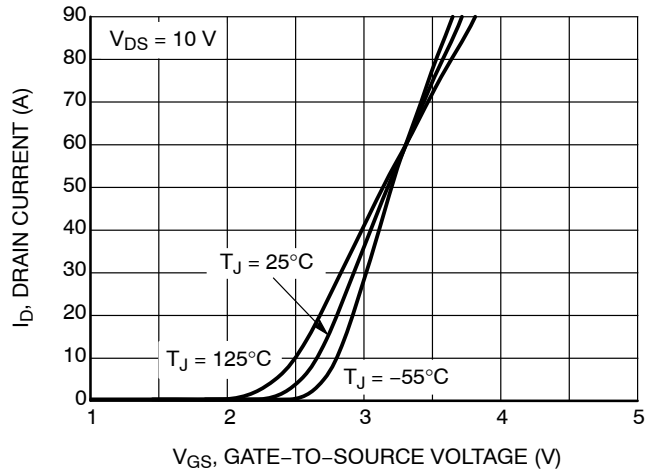


Figure 2. Transfer Characteristics

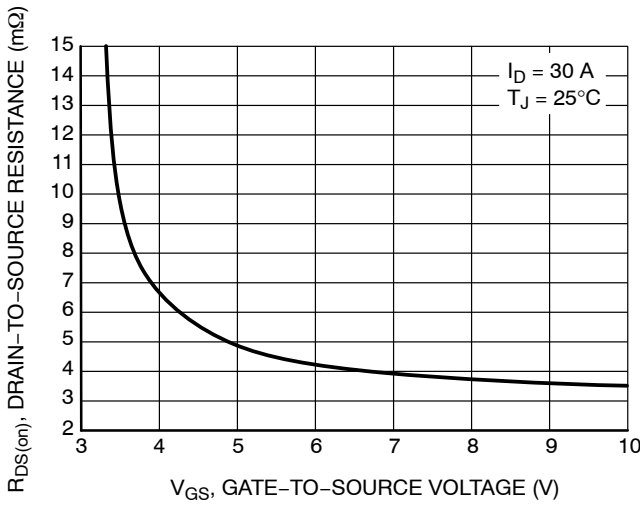


Figure 3. On-Resistance vs. Gate-to-Source Voltage

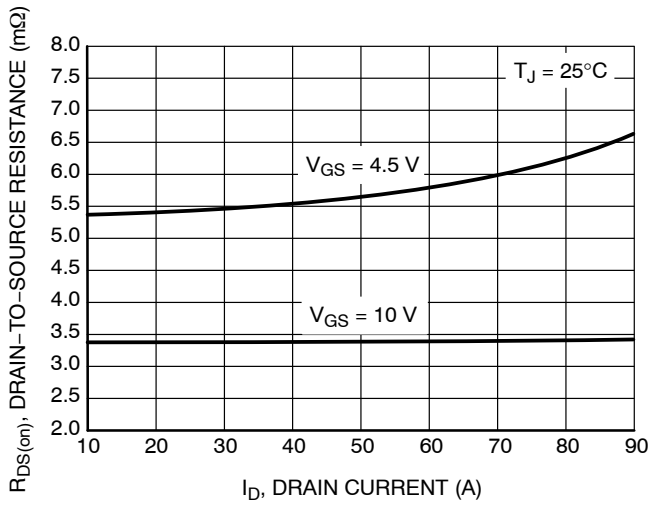


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

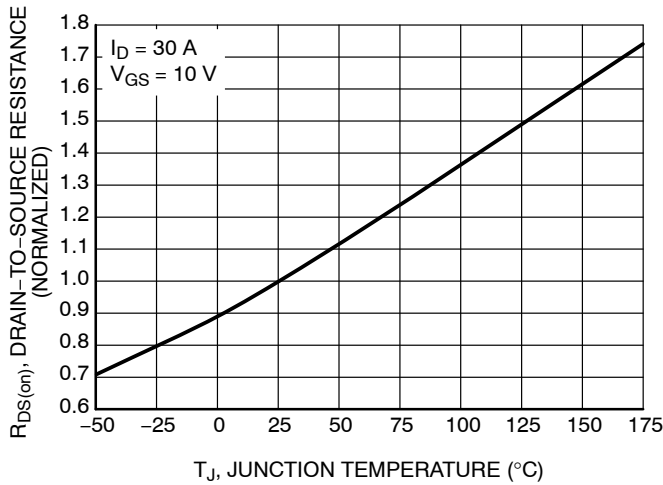


Figure 5. On-Resistance Variation with Temperature

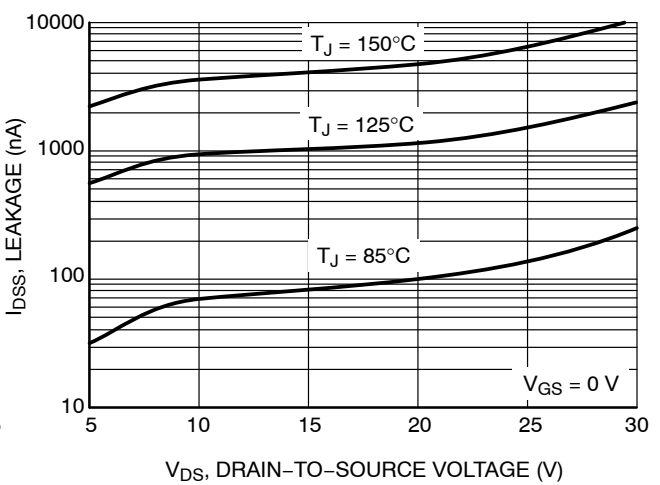


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTD4965N

TYPICAL PERFORMANCE CURVES

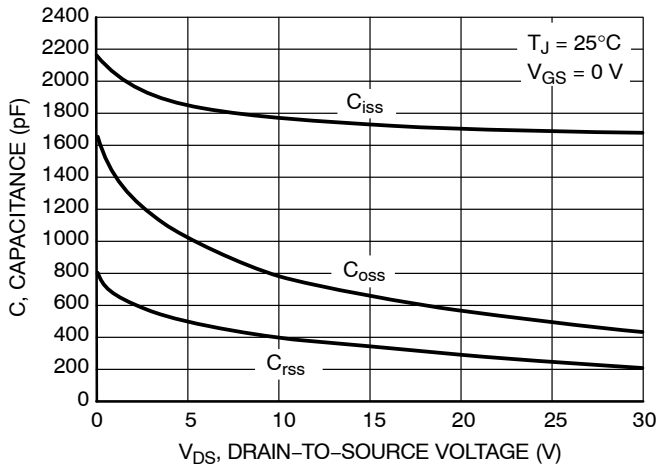


Figure 7. Capacitance Variation

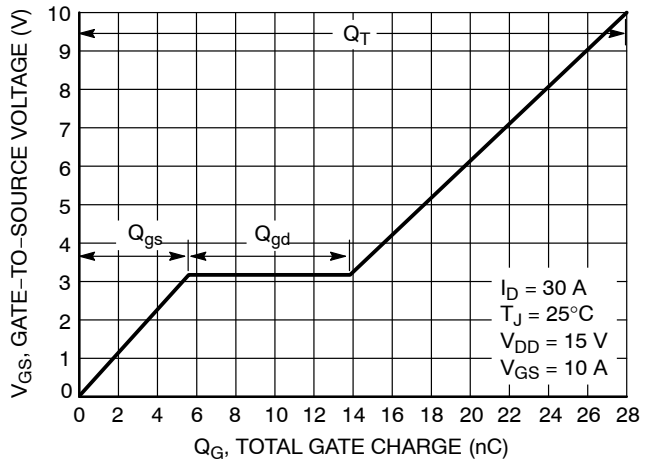


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

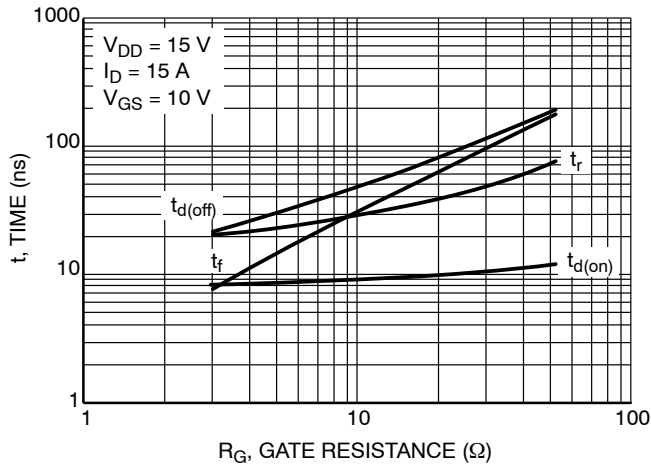


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

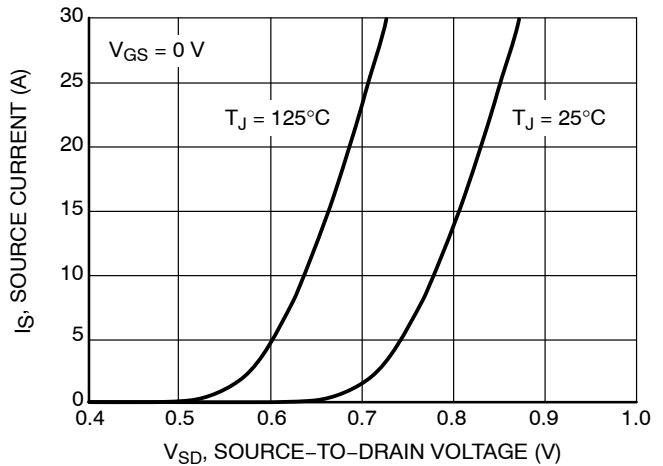


Figure 10. Diode Forward Voltage vs. Current

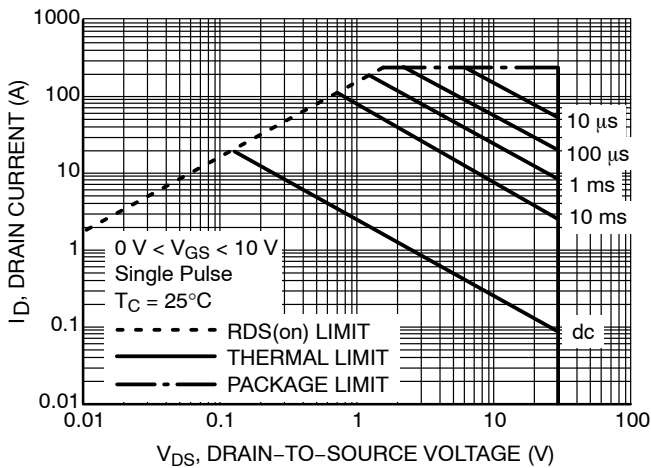


Figure 11. Maximum Rated Forward Biased Safe Operating Area

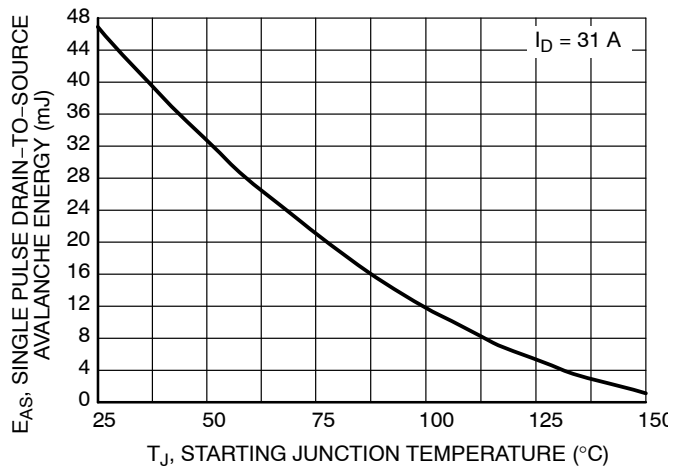
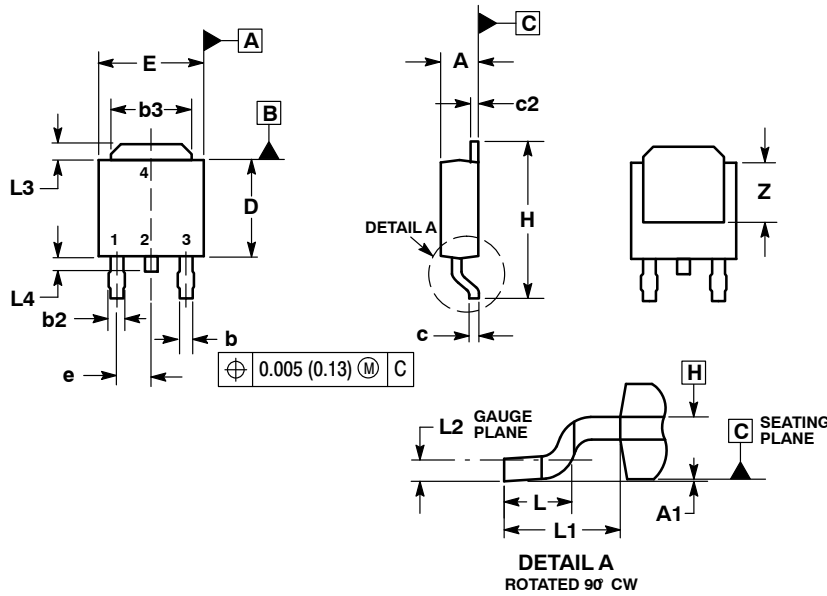


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

NTD4965N

PACKAGE DIMENSIONS

DPAK (SINGLE GUAGE) CASE 369AA ISSUE B

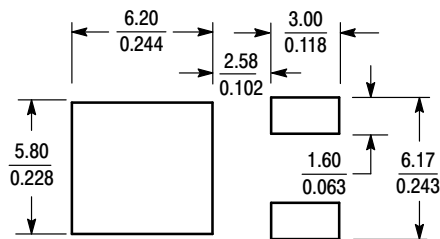


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

STYLE 2:

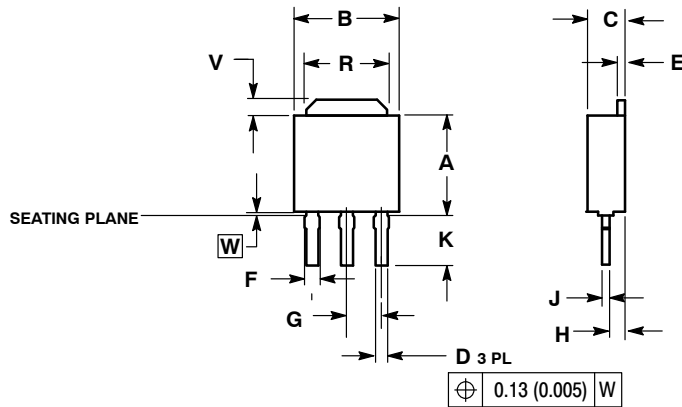
- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NTD4965N

PACKAGE DIMENSIONS

3 IPAK, STRAIGHT LEAD CASE 369AC ISSUE O

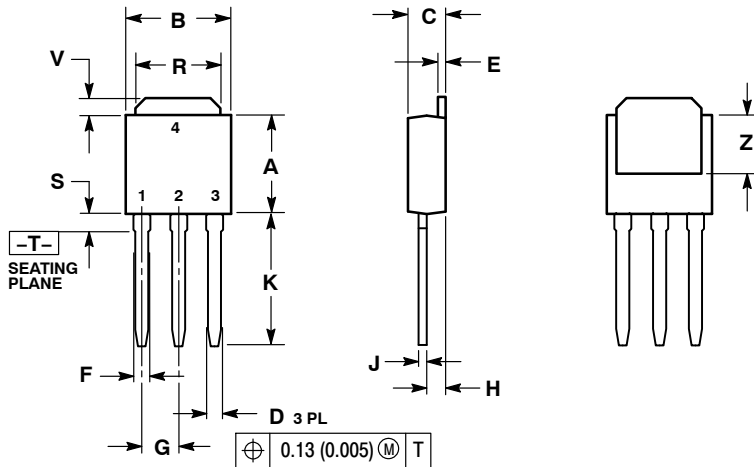


NOTES:

- 1.. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2.. CONTROLLING DIMENSION: INCH.
3. SEATING PLANE IS ON TOP OF DAMBAR POSITION.
4. DIMENSION A DOES NOT INCLUDE DAMBAR POSITION OR MOLD GATE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.043	0.94	1.09
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.134	0.142	3.40	3.60
R	0.180	0.215	4.57	5.46
V	0.035	0.050	0.89	1.27
W	0.000	0.010	0.000	0.25

IPAK CASE 369D ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

ON Semiconductor and **ON** are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [ON Semiconductor](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [IRFD120](#) [JANTX2N5237](#) [FCA20N60_F109](#) [FDZ595PZ](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [TPCC8103,L1Q\(CM](#)
[MIC4420CM-TR](#) [VN1206L](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [SSM6J414TU,LF\(T](#) [751625C](#) [BUK954R8-60E](#)
[NTE6400](#) [SQJ402EP-T1-GE3](#) [2SK2614\(Te16L1,Q\)](#) [2N7002KW-FAI](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [ECH8691-TL-W](#)
[FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE221](#) [NTE2384](#) [NTE2903](#) [NTE2941](#) [NTE2945](#) [NTE2946](#) [NTE2960](#) [NTE2967](#)
[NTE2969](#) [NTE2976](#) [NTE455](#) [NTE6400A](#) [NTE2910](#) [NTE2916](#) [NTE2956](#) [NTE2911](#) [DMN2080UCB4-7](#) [TK10A80W,S4X\(S](#)
[SSM6P69NU,LF](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#)